

S/N Unknown

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Kie Y. Ahn et al.

Examiner: Unknown

Serial No.: Unknown

Group Art Unit: Unknown

Filed: Herewith

Docket: 303.678US4

Title: STRUCTURE AND METHOD FOR DUAL GATE OXIDE THICKNESSES

PRELIMINARY AMENDMENT

BOX PATENT APPLICATION

Commissioner for Patents

Washington, D.C. 20231

Sir:

Prior to taking up the above-identified patent application for examination, please amend the application as follows:

IN THE SPECIFICATION

On page 1, line 3, before the heading, "Field of the Invention", insert the following paragraph:

Cross Reference to Related Application(s)

This application is a division of U.S. Patent Application No. 09/514,629, filed on February 28, 2000, the specification of which is incorporated herein by reference.

IN THE CLAIMS

Please cancel claims 1 - 40, without prejudice or disclaimer, after adding the following new claims.

a logic device, wherein the logic device includes a transistor with a dielectric layer including:

a first dielectric layer of a first thickness less than 5 nanometers;

a top layer which exhibits a high resistance to oxidation at high temperatures; and

a memory device coupled to the logic device, wherein the memory device further includes a transistor with a second dielectric layer having a second thickness greater than the dielectric layer of the first thickness.

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